HIGH POWER AUDIO AMPLIFIERS WITH SHORT CIRCUIT PROTECTION

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This application note describes a recommended circuit approach for high-performance audio amplifiers in the 35-W to 100-W rms power range. Circuitry is included which enables the amplifier to operate safely under any load condition including a continuous short.
INTRODUCTION

The development of Motorola's 200-W PNP silicon power transistors now allows the economical design of full complementary direct-coupled audio amplifiers capable of delivering 100 watts of rms power into an 8-ohm load at less than 0.2% distortion.

The circuit approach suggested in this paper allows the designer to make optimum use of economy transistors in amplifiers that will operate safely under any usable load condition, including a short.

Tables are included which provide the designer with the necessary information to design 35-, 50-, 60-, 75-, and 100-watt amplifiers at either 4 or 8 ohm load impedance. Detailed design information is included in the appendix for those who wish to design amplifiers for power outputs other than those shown.

CIRCUIT DESCRIPTION

The schematic diagram shown in Figure 1 is the recommended approach for the full-complementary amplifier with short-circuit protection.

Transistors Q1, Q2, Q4, Q6, Q7, Q8, Q9, and Q10, along with their associated components, comprise the standard full-complementary circuit. Transistors Q1 and Q2 are used in a differential amplifier configuration which, when used with a split power supply, provide a convenient means for setting the dc voltage level at the output at zero, enabling the amplifier to be direct coupled to the speaker. Resistor Rf provides 100% dc feedback from the output to the input, for excellent dc stability. The resistance ratio of Rf to R1 determines the closed-loop ac-voltage gain of the amplifier. Transistor Q4 functions as a high-gain, common-emitter driver. Since the output configura-

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**NOTE 1:** All of the resistors with the values shown are ± 10% tolerance, except where * indicates ± 5%.

1. L1 is #20 wire close-wound for the full length of resistor, R16.

**FIGURE 1 — Schematic Diagram of 35- to 100-W Amplifiers. Parts Values are Shown in Tables 1, 2 and 3.**

Circuit diagrams external to Motorola products are included as a means of illustrating typical semiconductor applications; consequently, complete information sufficient for construction purposes is not necessarily given. The information in this Application Note has been carefully checked and is believed to be entirely reliable. However, no responsibility is assumed for inaccuracies. Furthermore, such information does not convey to the purchaser of the semiconductor devices described any license under the patent rights of Motorola Inc. or others.
tion serves only as an emitter follower, this transistor must be capable of handling the full-load voltage swing. Transistor Q6 serves as a constant-current source for the dc bias current, which flows through Q4 and the dual bias diode, D2. This transistor, Q6, also eliminates the need for the large bootstrap electrolytic capacitor commonly used to provide ac current drive to the lower half of the output circuit during negative peak signal excursions. Transistors Q7 and Q8 form a compound pair which function as an emitter follower with high current gain and unity voltage gain for the positive portion of the output signal. Q9 and Q10 similarly function for the negative portion of the output signal. The zener diode, D1, is used to set the dc current through the differential amplifier and provide ac hum rejection from the negative power supply.

SHORT-CIRCUIT PROTECTION

Semiconductors Q3, Q5, Q11, Q12, D3, and D4, along with their associated resistors, comprise the short-circuit protection network.

The resistors R8, R10, R11, and R12, form a voltage-summing network. The voltage appearing at the base of transistor Q11 is thus determined by the collector current of Q8 flowing through resistor R6 and the voltage appearing from +VCC to the output. This summing network, since it detects both the voltage and current of Q8, effectively senses the peak power dissipation occurring in this transistor. At a predetermined power level in transistor Q8, the summing network can be chosen so that transistor Q11 conducts sufficiently to turn on transistor Q3. Transistor Q3 then steals the drive current from the base of transistor Q4, and hence limits the power dissipated in Q8. Diode D3 is used to prevent transistor Q11 from turning on, under normal load conditions, when the output signal swings negative. Resistors R9, R13, R14, R15, along with transistors Q12, Q5, and diode D4, similarly limit the power dissipation occurring in the output transistor Q10.

TABLE 1 – Semiconductor Complement

<table>
<thead>
<tr>
<th>Output Power (Watts-mms)</th>
<th>Load Impedance (Ohms)</th>
<th>Output Transistors</th>
<th>Driver Transistors</th>
<th>Pre-Driver Transistors</th>
<th>Differential Amplifier Transistors (Q1 &amp; Q2)</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
<td>NPN (Q10)</td>
<td>PNP (Q8)</td>
<td>NPN (Q7)</td>
<td>PNP (Q9)</td>
</tr>
<tr>
<td>35</td>
<td>4</td>
<td>MJ2840</td>
<td>MJ2940</td>
<td>MPSU05</td>
<td>MPSU55</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>MJE2801</td>
<td>MJE2901</td>
<td>MPSU05</td>
<td>MPSU55</td>
</tr>
<tr>
<td>50</td>
<td>4</td>
<td>2N5302</td>
<td>2N4399</td>
<td>MPSU05</td>
<td>MPSU55</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>MJ2841</td>
<td>MJ2941</td>
<td>MPSU06</td>
<td>MPSU56</td>
</tr>
<tr>
<td>60</td>
<td>4</td>
<td>2N5302</td>
<td>2N4399</td>
<td>MPSU06</td>
<td>MPSU56</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>MJ2841</td>
<td>MJ2941</td>
<td>MPSU06</td>
<td>MPSU56</td>
</tr>
<tr>
<td>75</td>
<td>4</td>
<td>MJ802</td>
<td>MJ4502</td>
<td>MPSU06</td>
<td>MPSU56</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>MJ802</td>
<td>MJ4502</td>
<td>MPSU06</td>
<td>MPSU56</td>
</tr>
<tr>
<td>100</td>
<td>4</td>
<td>MJ802</td>
<td>MJ4502</td>
<td>MPSU06</td>
<td>MPSU56</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>MJ802</td>
<td>MJ4502</td>
<td>MPSU06</td>
<td>MPSU56</td>
</tr>
</tbody>
</table>

The following semiconductors are used at all of the power levels:
Q11 – MPSL01
Q5 – MPSA20
Q12 – MPSL51
Q3 – MPSA70

NOTE 1: For a low-cost zener diode, an emitter-base junction of a silicon transistor can be substituted. A transistor similar to the MPS6512 can be used for the 7.5 V zener. A transistor similar to the Motorola BC317 can be used for the 10 V zener diode.
TABLE 2 — Resistor Values and Power Supply Voltages

<table>
<thead>
<tr>
<th>Output Power (Watts-rms)</th>
<th>Load Impedance (Ohms)</th>
<th>R1 ±5%</th>
<th>R2 ±10%</th>
<th>R3 ±5%</th>
<th>R4 ±5%</th>
<th>R5 ±5%</th>
<th>R6, R7 ±10%</th>
<th>R8, R9 ±5%</th>
<th>R10, R15 ±5%</th>
<th>R11, R14 ±5%</th>
<th>R12, R13 ±5%</th>
<th>VCC</th>
</tr>
</thead>
<tbody>
<tr>
<td>35</td>
<td>4</td>
<td>820</td>
<td>2.7 k</td>
<td>18 k</td>
<td>1.2 k</td>
<td>120</td>
<td>0.39</td>
<td>390</td>
<td>2.7 k</td>
<td>1.5 k</td>
<td>470</td>
<td>±21 V</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>560</td>
<td>3.9 k</td>
<td>22 k</td>
<td>1.2 k</td>
<td>180</td>
<td>0.47*</td>
<td>240</td>
<td>3.0 k</td>
<td>1.2 k</td>
<td>470</td>
<td>±27 V</td>
</tr>
<tr>
<td>50</td>
<td>4</td>
<td>680</td>
<td>3.3 k</td>
<td>22 k</td>
<td>1.2 k</td>
<td>100</td>
<td>0.33</td>
<td>360</td>
<td>3.3 k</td>
<td>1.5 k</td>
<td>470</td>
<td>±25 V</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>470</td>
<td>4.7 k</td>
<td>27 k</td>
<td>1.2 k</td>
<td>150</td>
<td>0.43*</td>
<td>270</td>
<td>3.9 k</td>
<td>1.2 k</td>
<td>470</td>
<td>±32 V</td>
</tr>
<tr>
<td>60</td>
<td>4</td>
<td>620</td>
<td>3.9 k</td>
<td>22 k</td>
<td>1.2 k</td>
<td>120</td>
<td>0.39</td>
<td>430</td>
<td>3.9 k</td>
<td>1.5 k</td>
<td>470</td>
<td>±27 V</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>430</td>
<td>5.6 k</td>
<td>33 k</td>
<td>1.2 k</td>
<td>120</td>
<td>0.39</td>
<td>300</td>
<td>4.7 k</td>
<td>1.2 k</td>
<td>470</td>
<td>±36 V</td>
</tr>
<tr>
<td>75</td>
<td>4</td>
<td>560</td>
<td>4.7 k</td>
<td>27 k</td>
<td>1.2 k</td>
<td>91</td>
<td>0.33</td>
<td>620</td>
<td>5.6 k</td>
<td>1.8 k</td>
<td>470</td>
<td>±30 V</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>390</td>
<td>6.8 k</td>
<td>33 k</td>
<td>1.2 k</td>
<td>150</td>
<td>0.39</td>
<td>390</td>
<td>6.8 k</td>
<td>1.5 k</td>
<td>470</td>
<td>±40 V</td>
</tr>
<tr>
<td>100</td>
<td>4</td>
<td>470</td>
<td>5.6 k</td>
<td>33 k</td>
<td>1.2 k</td>
<td>68</td>
<td>0.39</td>
<td>1.0 k</td>
<td>8.2 k</td>
<td>2.2 k</td>
<td>470</td>
<td>±34 V</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>330</td>
<td>8.2 k</td>
<td>39 k</td>
<td>1.2 k</td>
<td>100</td>
<td>0.39</td>
<td>510</td>
<td>9.1 k</td>
<td>1.8 k</td>
<td>470</td>
<td>±45 V</td>
</tr>
</tbody>
</table>

NOTE: All of the above resistor values are in ohms and are 1/2 W except for R6 and R7.
* R6 and R7 are 5 W resistors except where * indicates 2 W.

AMPLIFIER OUTPUT LOAD AND TRANSISTOR POWER DISSIPATION CONSIDERATIONS

High-fidelity speaker systems can appear capacitive or inductive as well as resistive. The current and voltage appearing in the amplifier will thus be out of phase when the load appears reactive. Evaluation of several speaker systems showed that nearly 60° of phase shift can occur between the voltage and current. At 60° phase shift, 1/2 VCC and the peak load current can appear simultaneously at the output transistor, or VCC and 1/2 the peak load current can appear, depending on whether the load is capacitive or inductive. Since the short-circuit-protection network must not interfere with normal operating load conditions, the minimum peak power level to which the short-circuit dissipation can be limited is the product of the peak current and voltage appearing at the output transistor under the worst-case allowable phase shift. This means that if we want to allow normal operation into a ±60° reactive load, our short-circuit power dissipation will be determined by the following equation:

\[
P_{PPD(\text{short circuit})} = \frac{V_{CC} \times I_{\text{peak}}}{2}
\]

where \( P_{PPD} \) is the peak dissipation for each output transistor; it is also the total average power dissipation for the amplifier.

The average power dissipation of each transistor is expressed by the equation:

\[
P_{AD(\text{short circuit})} = \frac{1/2 V_{CC} \times I_{\text{peak}}}{2}
\]

The worst-case average power dissipation in driver transistors Q7 and Q9 is the power dissipation expressed in Equation 2 divided by the current gain of the output trans-

TABLE 3 — Transistor Heat Sink Requirements

<table>
<thead>
<tr>
<th>Output Power (Watts-rms)</th>
<th>Load Impedance (Ohms)</th>
<th>Output Transistor Heat Sink ((\theta_{CA})) (See Note 1)</th>
<th>Driver Transistor Heat Sink ((\theta_{CA})) (See Note 2)</th>
</tr>
</thead>
<tbody>
<tr>
<td>35</td>
<td>4</td>
<td>4.2°C/W</td>
<td>None</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>2.4°C/W</td>
<td>None</td>
</tr>
<tr>
<td>50</td>
<td>4</td>
<td>3.0°C/W</td>
<td>60°C/W</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>2.4°C/W</td>
<td>60°C/W</td>
</tr>
<tr>
<td>60</td>
<td>4</td>
<td>2.5°C/W</td>
<td>60°C/W</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>2.0°C/W</td>
<td>60°C/W</td>
</tr>
<tr>
<td>75</td>
<td>4</td>
<td>1.6°C/W</td>
<td>35°C/W</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>1.6°C/W</td>
<td>70°C/W*</td>
</tr>
<tr>
<td>100</td>
<td>4</td>
<td>1.0°C/W</td>
<td>20°C/W</td>
</tr>
<tr>
<td></td>
<td>8</td>
<td>1.0°C/W</td>
<td>50°C/W*</td>
</tr>
</tbody>
</table>

NOTE 1: All of the output transistors are in TO-3 packages with the exception of the MJ2801/2901 (35 W/BΩ), which are in the Case 90 Thermopack® plastic package.

NOTE 2: All of the driver transistors are in the plastic Uniwatt™ package with the exception of those marked * which are metal cased TO-5.

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sistor. Because of the nature of the short-circuit-protection network, the minimum 1-second safe-operating-area requirement for the output transistor occurs at \( V_{CC} \) and is the same as the peak dissipation as determined by Equation 1. The maximum thermal resistance, and consequently the minimum power dissipation rating, required for each output transistor is found by the following equations

\[
\theta_{JC(max)} = \frac{T_J(max) - T_A}{\theta_{CA} \times P_{AD}}
\]  

where \( T_J(max) \) is the maximum junction temperature rating of the device,

\( T_A \) is the maximum ambient temperature, and

\( \theta_{CA} \) is the thermal resistance of the heat sink including the mica insulating washer, if used.

The minimum power dissipation rating of the transistor is found by

\[
P_{DM} = \frac{T_J(max)}{\theta_{JC(max)}}
\]

**COMPONENT VALUES**

Table 1 lists the specific resistor values for 4- and 8-ohm amplifiers at 35-, 50-, 60-, 75-, and 100-watt power levels. Table 2 lists the semiconductors required for the same amplifiers. The numbers given in this chart are the nearest standard parts available that will meet or exceed the minimum specifications required for the particular amplifier. Where large amplifier production quantities are involved, the transistor manufacturer should be consulted for the optimum transistor specifications to realize maximum cost savings.

Table 3 lists the minimum heat-sink requirements for the amplifier transistors.

**PERFORMANCE**

All of the amplifiers listed in Tables 1 and 2 will perform typically as shown as follows:

Output Power: Each amplifier will deliver its full rated rms output power into the nominal load impedance providing the power supply has adequate regulation. Figure 2 shows the power output versus load impedance.

Input Sensitivity: 1 V\(_{rms}\) into 10 k\(\Omega\) for full rated output power.

Frequency Response: Less than 3-dB rolloff from 10 Hz to 100 kHz referenced to 1 kHz.

Power Bandwidth: Full rated output power ±1/2 dB from 20 Hz to 20 kHz. (See Figure 3)

Total Harmonic Distortion: Less than 0.2% at any power level between 100 mW and full rated output and at any frequency between 20 Hz and 20 kHz. (See Figure 4)

Intermodulation Distortion: Less than 0.2% at any power level from 100 mW to full rated output. (60 Hz and 7 kHz mixed 4 to 1)

Damping Factor: Over 150 at any frequency from 20 Hz to 20 kHz.

Square Wave Response: (See Figure 5)

Short Circuit Power Dissipation in Each Output Transistor: (See Figure 6)

**FIGURE 5 — Square Wave Response**

**Design Example**

An electronics company has a requirement for a direct-coupled audio amplifier with the following specifications:

Power Output: 60 watts \( V_{rms} \) into 8 \( \Omega \) with normal operation allowed into ±60° reactive load.

Short-Circuit Operation: Circuit has to operate safely at 50°C ambient temperature with the output shorted.

Total Distortion: Less than 0.2%.
Input Sensitivity: \( 1 \ V_{\text{rms}} \) (1.4 \( V_{\text{peak}} \)) input for 60 watts into 8 \( \Omega \).

The designer chooses a full-complementary circuit, similar to the circuit of Figure 1, due to its excellent ac and dc performance.

The circuit values are determined as follows:

\[
R_1 = \frac{\text{peak input voltage}}{R_f} \times R_f
\]

\[
R_f = 10 \ \text{k}\Omega \text{. The rms load voltage can be found by}
\]

\[
P = \frac{V_{\text{rms}}^2}{R_L}
\]

Since \( P = 60 \text{ W} \) and \( R_L = 8 \ \Omega \),

\[
V_{\text{rms}} = \sqrt{60 \cdot 8} = 21 \text{ V}, \text{ and}
\]

\[
V_{\text{peak}} = 1.4 \times V_{\text{rms}} = 31 \text{ V}.
\]

Therefore \( R_1 = \frac{1.4}{31} \times 10 \ \text{k}\Omega = 450 \ \Omega \).

The differential amplifier must be biased for 2 mA through the emitter leg with 680 \( \Omega \) in the collector circuit. 2 mA is sufficient for good zener diode regulation.

\[
R_2(\text{max}) = \frac{36 - 10}{0.004} = 6.5 \ \text{k}\Omega
\]

The nearest standard value is 5.6 \( \text{k}\Omega \).

R3, R4, R5: The voltage at the base of Q6 with respect to the negative supply voltage should be kept under 2.0 V to prevent premature clipping of the negative portion of the output signal.

Therefore, if \( \frac{R_4}{R_3 + R_4} \times V_{\text{CC}} \) is set equal to 1.3 V, and letting

\[
R_4 = 1.2 \ \text{k}\Omega,
\]

\[
\frac{1.2}{(R_3 + 1.2 \ \text{k})} \times 36 = 1.3, \text{ and} \]

\[
R_3 = 33 \ \text{k}\Omega \text{ (Nearest standard value)}
\]

Now, \( \frac{R_4}{R_3 + R_4} \times V_{\text{CC}} = \frac{1.2}{33 + 1.2} \times 36 = 1.26 \text{ V} \)

\[
R_5(\text{max}) = \frac{1.26 - V_{\text{BE}(Q6)}}{\text{Max dc Bias Current of Q4 + 1 mA}} \]

1 mA extra current allows for resistor tolerances.

Max dc Bias Current = \( \frac{I_{\text{peak load}}}{h\text{FE min(Q9)} \times h\text{FE min(Q10)}} \)

\[
I_{\text{peak load}} = \frac{V_{\text{peak}}}{R_L}
\]

\[
= \frac{31}{8} = 3.9 \ \text{A}
\]

\[
R_5(\text{max}) = \frac{0.61}{4.9 \text{ mA}} = 125 \ \Omega
\]

Choosing the nearest standard value, \( R_5 = 120 \ \Omega \)

R6, R7: Due to the nature of the short-circuit-protection network, the voltage appearing across R6 and R7, resulting from the peak load current, should be in the 1.5-to-2.0 V range.
\[ R_6 = R_7 \approx 1.5 \text{ V} \]
\[ R_6 = 3.9 \text{ A} \]
\[ R_6 = R_7 = 0.39 \text{ } \Omega \]

Short Circuit Protection Network
Refer to Figures 1 and 7.

R8, R10, R11, R12:
\[ V_{B11} \text{ has to be approximately } 1.4 \text{ V} \text{ for Q3 to conduct.} \]

![Figure 7 - Determining Values of Short-Circuit Network](image)

The maximum current-voltage product appearing at Q8 under normal load conditions occurs at the +60° phase shift limit of the reactive load.

For 60° phase shift, the following equations can be derived for turning Q3 on during shorted output:

\[ V_{B11} = \frac{1}{2} K_1 V_{R6(max)} + K_2 V_{EO(max)} \]  

(a)

\[ V_{B11} = K_1 V_{R6(max)} + \frac{1}{2} K_2 V_{EO(max)} \]  

(b)

where

\[ K_1 = \frac{R_{12}}{R_8 + R_{12}} \]

(c)

Solving (a) and (b) simultaneously yields:

\[ K_1 V_{R6(max)} = K_2 V_{EO(max)} \]

Since \[ V_{B11} = 1.4 \text{ V} \], and substituting equation (c) in equation (a) or (b), yields

\[ K_1 V_{R6(max)} = K_2 V_{EO(max)} = 0.933 \]  

(d)

Now under shorted output,

\[ V_{EO(max)} = V_{CC} = 36 \text{ V} \text{, and} \]

\[ V_{R6(max)} = I_{peak} R_E = 3.9 \text{ A} \times 0.39 \text{ } \Omega = 1.53 \text{ V} \]

Therefore, \[ \frac{R_{12}}{R_8 + R_{12}} \times 1.53 = 0.933 \text{ from equation(d).} \]  

(e)

If we let \[ R_{12} = 470 \text{ } \Omega \], a convenient value, then solving (e) yields:

\[ R_8 = 300 \text{ } \Omega \]

Let \[ R_{12'} = \frac{R_{12} \times R_8}{R_{12} + R_8} = 183 \text{ } \Omega \]

Then, \[ K_2 V_{EO(max)} = \frac{R_{12'}}{R_{12'} + R_{11} + R_{10}} \]

(f)

Also \[ \frac{R_{12'}}{R_{12'} + R_{11}} \times V_{D3} = 0.933 \text{ in order for the zener diode to conduct.} \]

Let \[ V_{D3} = 7.5 \text{ V} \], a convenient value for an economical zener diode.

For equation (f), \[ \frac{183}{183 + 1.2 k + R_{10}} \times 36 = 0.933 \], so

\[ R_{10} = 5.67 \text{ k} \Omega \]

![Figure 8 - Connections for the MFC8001 Dual Differential Amplifier](image)

To allow \[ V_{D3} \text{ to turn on at 10% high line voltage, } R_{10} \text{ should be reduced by 10% so let } R_{10} = 4.7 \text{ k} \Omega \].

Thus the values for the resistors in the short circuit network are:

\[ R_6 = R_7 = 0.39 \text{ } \Omega \]
\[ R_8 = R_9 = 300 \text{ } \Omega \]
\[ R_{10} = R_{15} = 5.6 \text{ k} \Omega \]
\[ R_{11} = R_{14} = 1.2 \text{ k} \Omega \]
\[ R_{12} = R_{13} = 470 \text{ } \Omega \]
TRANSISTOR BASIC REQUIREMENTS

Output Transistors
Q11, Q12: \( BV_{CEO} \geq 80 \text{ V at } I_C = 200 \text{ mA (allowing for } 10\% \text{ high line voltage)} \)
\[ h_{FE} = 20 \text{ minimum at } I_C = 4.0 \text{ A and } V_{CE} = 2.0 \text{ V} \]
The Motorola MJ2841 and MJ2941 meet these specs. The power dissipation rating is 150 watts and the maximum junction temperature is 200°C.
\[ \theta_J = \frac{200^\circ C - 25^\circ C}{150} = 1.1^\circ C/W, \]
where \( \theta_J \) = thermal resistance from junction to case for the transistor.
From equation (2), the power dissipation occurring in each output transistor during shorted load conditions is
\[ P_D = \frac{1}{2} V_{CC} \times 3.9 \text{ A} \times \frac{46}{2} = 35.1 \text{ watts} \]
Allowing for a 30% increase in \( P_D \) due to high line voltage, dc idling-power and component tolerance, \( P_{D(max)} \) is:
\[ P_{D(max)} = 46 \text{ watts.} \]
Allowing for 50°C ambient temperature:
\[ \theta_{CA} \text{ of heat sink} = \frac{T_J - T_A - P_{D(max)} \times \theta_J}{P_{D(max)}} \]
\[ = \frac{200 - 50 - 46 \times 1.17}{46} \times \frac{1}{1.03} = 2.0^\circ C/W \]

Driver Transistors
Q7 and Q9: \( BV_{CEO} \geq 80 \text{ V at } I_C = 10 \text{ mA} \)
\[ h_{FE} \geq 50 \text{ at } I_C = 100 \text{ mA} \]
The Motorola MPS-U06 and MPS-U56 transistors meet these requirements.
The maximum power dissipation rating of these devices is 5.0 watts and \( T_J(max) = 135^\circ C \).
\[ \theta_J = \frac{135 - 25}{5} = 22^\circ C/W \]
The maximum power dissipation in the driver transistor is:
\[ P_{D(max)} \text{ of driver} = \frac{h_{FE}}{2} \times I_{short} \times V_{CE} \]
\[ I_{short} = \frac{46 \text{ W}}{40 \text{ V}} = 2.3 \text{ A (at high line voltage).} \]

Therefore, \( P_D(\text{driver}) = \frac{46}{45} = 1.03 \text{ W.} \)
\[ \theta_{CA} \text{ of heat sink} = \frac{135 - 50 - (22 \times 1.03)}{1.03} = 60^\circ C/W \]
\[ \theta_{CA} = 60^\circ C/W \]

Pre-Driver Transistor
Q4 and Q9: \( BV_{CEO} \geq 80 \text{ V} \)
\[ h_{FE} \geq 75 \text{ at } I_C = 10 \text{ mA} \text{ and } V_{CE} = 1 \text{ V} \]

The Motorola MPS-A06 and MPS-A56 meet these requirements. The maximum power dissipation rating on this device is 500 mW and \( T_J(max) = 135^\circ C \).
\[ P_D(\text{pre-driver}) = \frac{P_D(\text{driver})}{h_{FE} \text{ of driver}} + P_{DC} \]
\[ P_{DC} \text{ is due to the bias current used in the calculation of R5 and is:} \]
\[ \frac{1030}{50} \text{ mW} + 40 \text{ V} \times 5 \text{ mA} = 220 \text{ mW} \]
\[ P_{D(max)} \text{ at } 50^\circ C \text{ for the transistor is:} \]
\[ 500 \text{ mW} - \frac{500 \text{ mW}}{135^\circ C} \times 50^\circ C = 315 \text{ mW} \]

Since this is greater than the worst-case dissipation, \( P_{D(pre-driver)} \), Q4 and Q9 do not require any heat sink.

DIFFERENTIAL AMPLIFIER
Q1 and Q2:
Since a dual-channel amplifier system was required, the MFC8001 dual differential amplifier was selected for Q1 and Q2 to realize minimum cost and space savings. The connections are shown in Figure 8.

SHORT-CIRCUIT PROTECTION TRANSISTORS
Q11, Q12, Q4, Q5:
All of these transistors operate at low current levels and can be TO-92 type plastic transistors.
Q11 and Q12 should have \( h_{FE} \geq 40 \text{ at } 2 \text{ mA and } BV_{CEO} \geq 80 \text{ V.} \)
The MPS-L01 and MPS-L51 meet these specifications.
Q4 and Q5 should have \( h_{FE} \geq 25 \text{ at } 1 \text{ mA and } BV_{CEO} \geq 10 \text{ V.} \) The MPS-A20 and MPS-A70 meet these specifications.
Now the designer has all of the component values and semiconductor types required for the 60-watt amplifier.